

KT962A-KT962B

ТРАНЗИСТОРЫ БОЛЬШОЙ МОЩНОСТИ СВЧ HIGH-POWER MICROWAVE TRANSISTORS

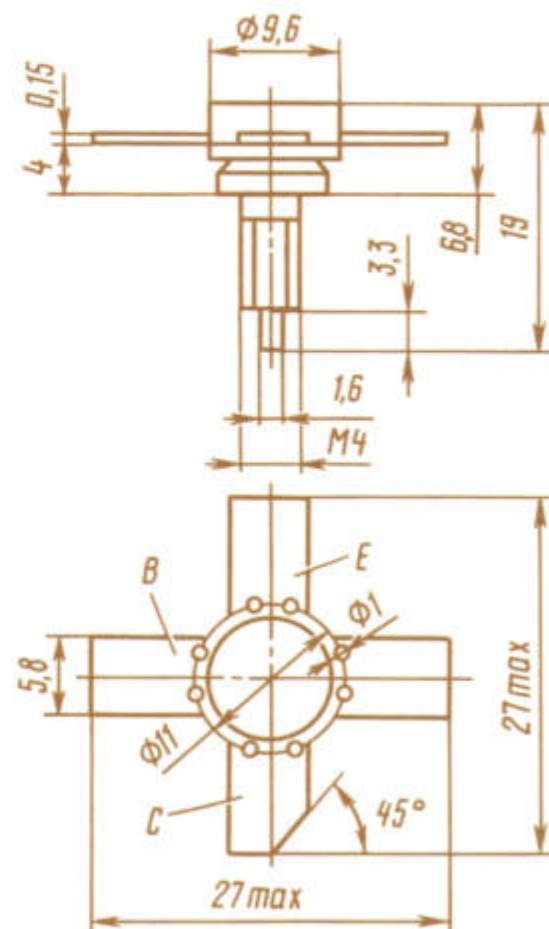
Транзисторы KT962A-KT962B предназначены для работы на частотах 400-1000 MHz в широкополосных усилителях мощности аппаратуры широкого применения.

Si-n-p-n-EP

The KT962A-KT962B transistors are designed for use in wideband power amplifiers at 400-1000 MHz in a wide range of applications.

МАКСИМАЛЬНО ДОПУСТИМЫЕ ДАННЫЕ $t_{case} = -40...+160^{\circ}C$ MAXIMUM RATINGS

$U_{CB\ max.}, V$	50
$U_{EB\ max.}, V$	4
$I_C\ max., A:$	
KT962A	1,5
KT962Б	2,5
KT962B	4
$P_C\ max.* (t_{case} \leq 40^{\circ}C), W:$	
KT962A	17
KT962Б	27
KT962B	66



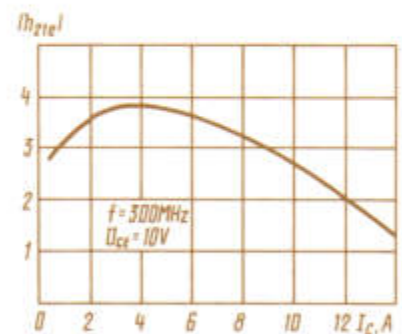
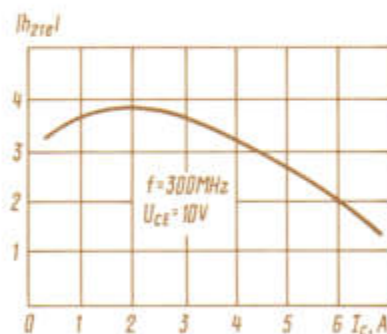
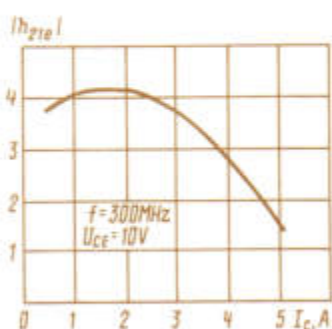
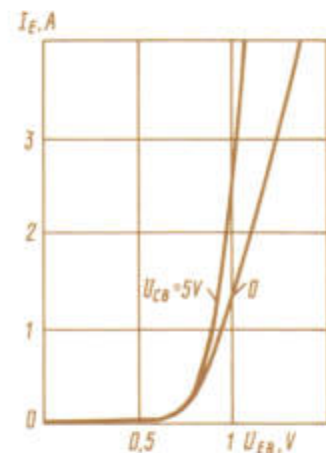
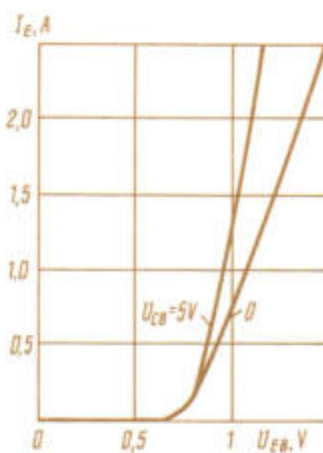
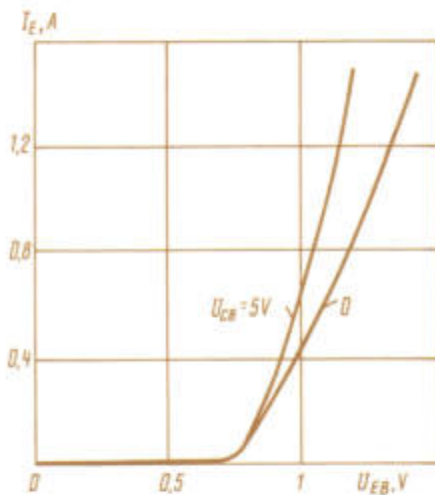
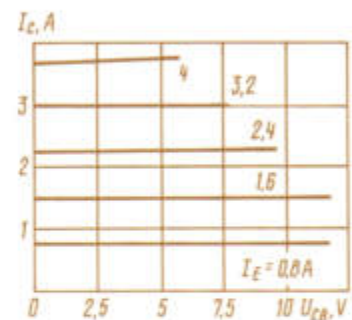
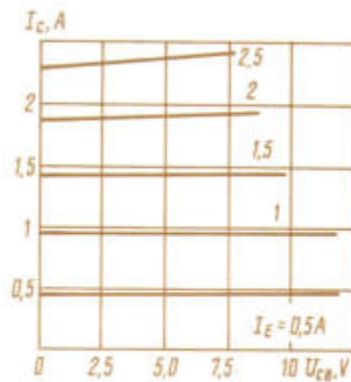
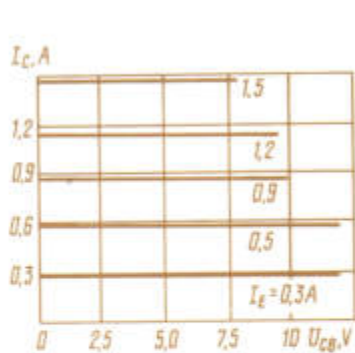
$t_{\text{max}}, ^\circ\text{C}$ 160

*Динамический режим.
Dynamic operation.

ЭЛЕКТРИЧЕСКИЕ ПАРАМЕТРЫ ELECTRICAL PARAMETERS

Параметры Parameters	KT962A	KT962B	KT962B	Режимы Conditions
1	2	3	4	5
$I_{\text{CBO}}, \text{mA}$	≤ 20	≤ 20	≤ 30	$U_{\text{CB}} = 50 \text{ V}$
$I_{\text{EBO}}, \text{mA}$	≤ 5	≤ 5	≤ 10	$U_{\text{EB}} = 4 \text{ V}$
$ h_{21e} $	$\geq 2,5$	$\geq 2,5$	≥ 2	$I_{\text{C}} = 1,5 \text{ A}$ $I_{\text{C}} = 1,8 \text{ A}$ $I_{\text{C}} = 3 \text{ A}$
				$U_{\text{CE}} = 10 \text{ V}$ $f = 300 \text{ MHz}$

1	2	3	4	5
C_{C}, pF	≤ 20	≤ 35	≤ 50	$U_{\text{CB}} = 28 \text{ V}$ $I_{\text{E}} = 0$ $f = 30 \text{ MHz}$
G_{p}	≥ 4	$\geq 3,5$	≥ 3	$P_{\text{out}} = 10 \text{ W}$ $P_{\text{out}} = 20 \text{ W}$ $P_{\text{out}} = 40 \text{ W}$
$\eta_{\text{C}}, \%$	≥ 36	≥ 40	≥ 40	$P_{\text{out}} = 10 \text{ W}$ $P_{\text{out}} = 20 \text{ W}$ $P_{\text{out}} = 40 \text{ W}$
				$U_{\text{CB}} = 28 \text{ V}$ $f = 1000 \text{ MHz}$



KT962A-KT962B

